FIG.1

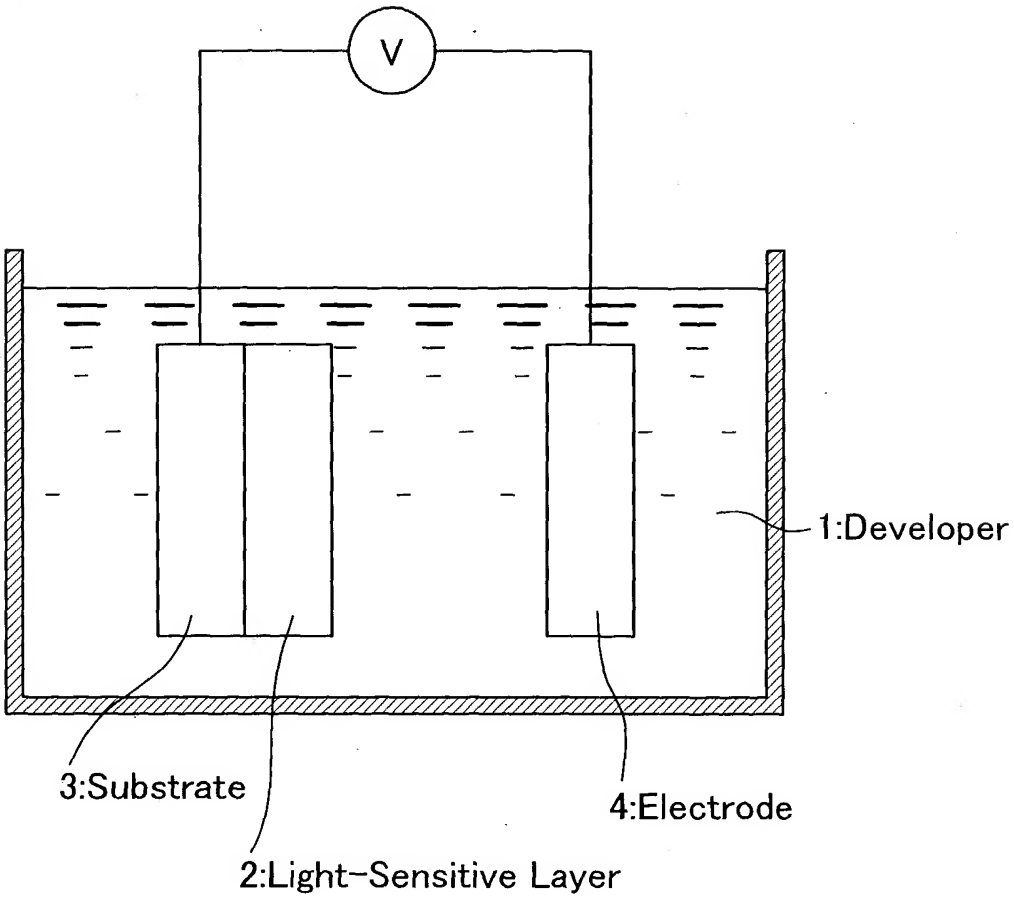
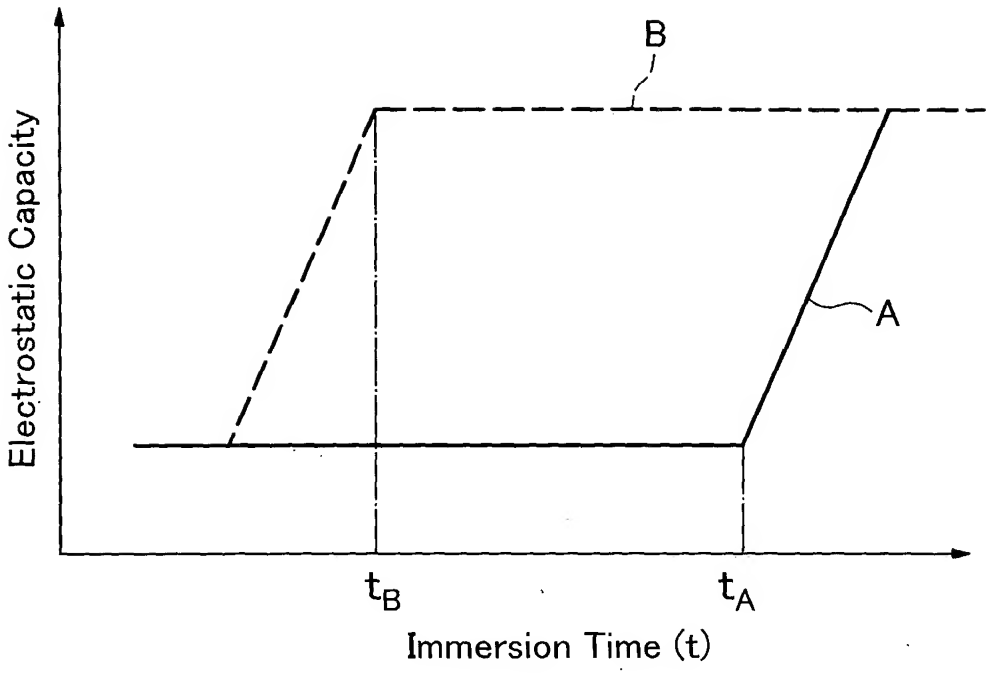

V
1:Developer
3:Substrate
2:Light-Sensitive Layer
4:Electrode

FIG.2



A : Light-Sensitive Layer Less Susceptible to Developer-Penetration
B : Light-Sensitive Layer Susceptible to Developer-Penetration
t_A : Time Elapsed Till the Electrostatic Capacity Undergoes a Change
t_B : Time Elapsed Till the Electrostatic Capacity Undergoes a Change

FIG.3

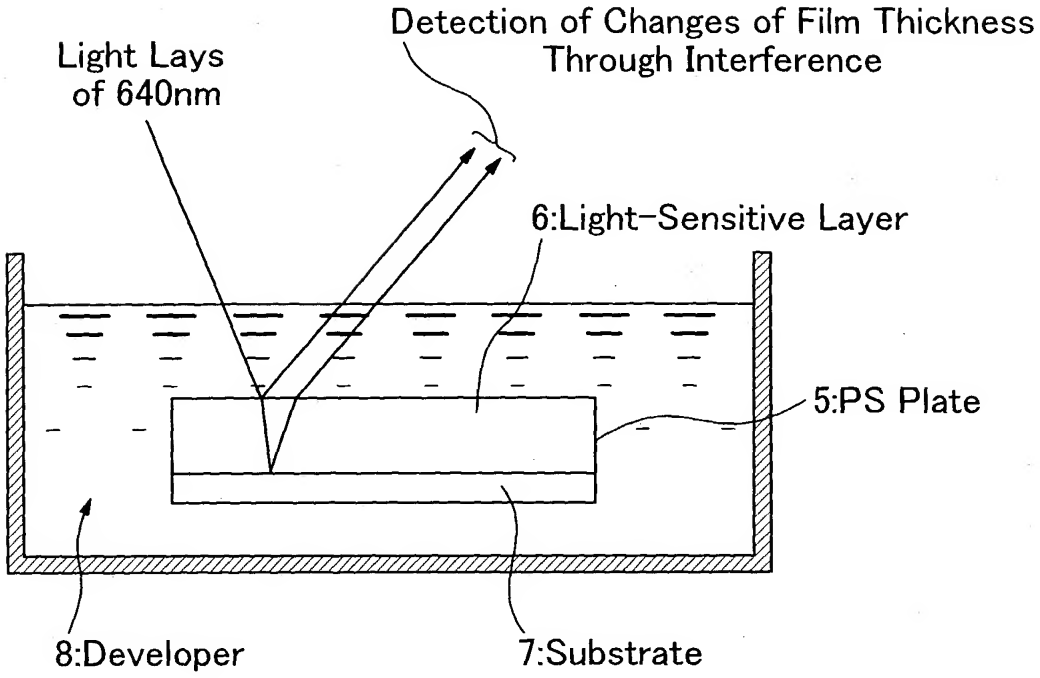
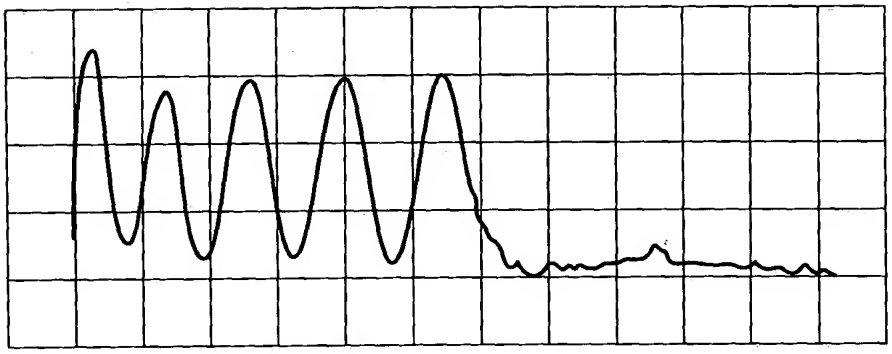

Detection of Changes of Film Thickness Through Interference
Light Lays of 640nm
6:Light-Sensitive Layer
5:PS Plate
8:Developer
7:Substrate

FIG.4A

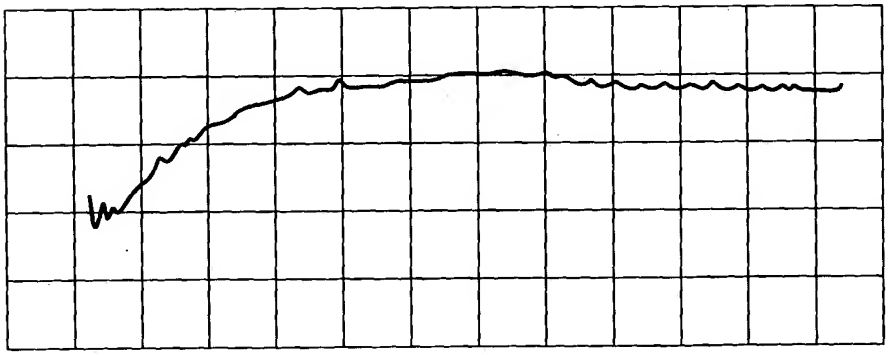
In Case of the Invention



time (There is observed interference waves.)

FIG.4B

In Case of the Conventional Technique



time (There is not observed any interference waves.)